

Chip Integration Technology Corporation

Super Low Barrier High Voltage Power Rectifier

Main Product Characteristics

I _{F(AV)}	20A		
V_{RRM}	50V		
T _J	150°C		
$V_{(Typ)}$	0.63V		

■ Features

- Low forward voltage drop.
- Excellent high temperature stability.
- · Fast switching capability.
- Suffix "G" indicates Halogen-free part, ex.CSP20S50SG-A.
- Lead-free parts meet environmental standards of MIL-STD-19500/228

■ Mechanical data

• Epoxy: UL94-V0 rated flame retardant.

• Case: Molded plastic, TO-277.

• Lead: Solder plated, solderable per MIL-STD-750, Method 2026.

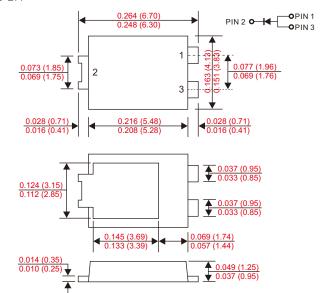
• Polarity: Indicated by cathode band.

• Mounting Position : Any.

• Weight: Approximated 0.093 grams.

Outline





Dimensions in inches and (millimeters)

■ Maximum ratings and electrical characteristics

Rating at 25°C ambient temperature unless otherwise specified. Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Parameter	Conditions	Symbol	CSP20S50S-A	
Marking code			CSP20S50S	UNIT
Peak repetitive reverse voltage		V _{RRM}		
Working peak reverse voltage		V _{RWM}	50	V
DC blocking voltage		V _{RM}		
RMS reverse voltage		V _{R(RMS)}	35	V
Forward rectified current		Io	20	А
Forward surge current	8.3ms single half sine-wave superimposed on rate load (JEDEC method)	I _{FSM}	350	Α
Thermal resistance	Junction to case	R _{eJC}	4	°C/W
Operating and Storage temperature		T_J, T_{STG}	-55 ~ +150	°C

Parameter	Conditions	Symbol	MIN.	TYP.	MAX.	UNIT
Reverse breakdown voltage	I _R = 0.5mA	= 0.5mA V _{(BR)R} 50			V	
E	$I_F = 20A, T_J = 25^{\circ}C$.,			500	mV
Forward voltage drop	$I_F = 20A, T_J = 125^{\circ}C$	V _F			460	
D	$V_R = V_{RRM} T_J = 25^{\circ}C$				0.5	
Reverse current	$V_R = V_{RRM} T_J = 125^{\circ}C$	I _R	100	100	mA	

Note: 1.FR-4 PCB, 2oz.Copper.
2.Polymide PCB, 2oz.Copper.Cathode pad dimensions 18.8mm x 14.4mm.Anode pad dimensions 5.6mm x 14.4mm.

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■ Rating and characteristic curves

Fig.1 - Forward Current Derating Curve 24 Average Forward Current, I_{F(AV)} (A) 20 16 12 8 4 0 <u></u>25 50 75 100 125 150 175 Case Temperature, T_c ($^{\circ}C$)

Fig. 2 - Instantaneous Forward Characteristics 100 Instantaneous Forward Current, $I_{\scriptscriptstyle F}\left(A\right)$ 10 T_A=150°C T_A=100°C 1 =75°C T_A=25°C 0.6 Instantaneous Forward Voltage, V_F (Volts)

Fig. 3 - Reverse Characteristics 100 Instantaneous Reverse Current, I_R (mA) 10 T_A=100°C T_A=75°C $T_A=50^{\circ}C$ 0.1 T_A=25°C 0.01 0 Reverse Voltage, $V_R(V)$

50

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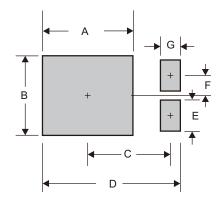
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■ TO-277 foot print



Α	В	С	D	Е	F	G
0.185 (4.70)	0.142 (3.60)	0.152 (3.87)	0.260 (6.60)	0.055 (1.40)	0.035 (0.90)	0.031 (0.80)

Dimensions in inches and (millimeters)

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